

**SOT-23 Formed SMD Package**

**BCW69  
BCW70**

*SILICON PLANAR EPITAXIAL TRANSISTORS*

*P-N-P transistors*

**Marking**

BCW69 = H1

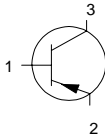
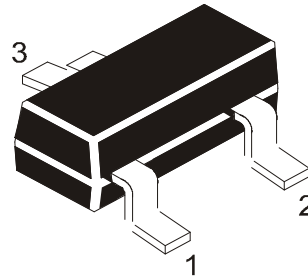
BCW70 = H2

**Pin configuration**

1 = BASE

2 = EMITTER

3 = COLLECTOR



**ABSOLUTE MAXIMUM RATINGS**

D.C. current gain at  $T_j = 25\text{ }^\circ\text{C}$

$-I_C = 2\text{ mA}; -V_{CE} = 5\text{ V}$

Collector-base voltage (open emitter)

Collector-emitter voltage (open base)

Collector current (peak value)

Total power dissipation up to  $T_{amb} = 25\text{ }^\circ\text{C}$

Junction temperature

Transition frequency at  $f = 35\text{ MHz}$

$-I_C = 10\text{ mA}; -V_{CE} = 5\text{ V}$

Noise figure at  $R_S = 2\text{ k}\Omega$

$-I_C = 200\text{ }\mu\text{A}; -V_{CE} = 5\text{ V};$

$f = 1\text{ kHz}; B = 200\text{ Hz}$

		<b>BCW69</b>	<b>BCW70</b>
$h_{FE}$	>	120	215
$h_{FE}$	<	260	500
$-V_{CB0}$	max.	50	V
$-V_{CE0}$	max.	45	V
$-I_{CM}$	max.	200	mA
$P_{tot}$	max.	250	mW
$T_j$	max.	150	$^\circ\text{C}$
$f_T$	typ.	150	MHz
F	<	10	dB

**BCW69**  
**BCW70**

**RATINGS** (at  $T_A = 25^\circ\text{C}$  unless otherwise specified)

*Limiting values*

Collector-base voltage (open emitter)	$-V_{CB0}$	max.	50 V
Collector-emitter voltage ( $V_{BE} = 0$ )	$-V_{CES}$	max.	50 V
Collector-emitter voltage (open base)			
$-I_C = 2 \text{ mA}$	$-V_{CE0}$	max.	45 V
Emitter-base voltage (open collector)	$-V_{EB0}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	max.	250 mW
Storage temperature	$T_{stg}$		$-55$ to $+150^\circ\text{C}$
Junction temperature	$T_j$	max.	$150^\circ\text{C}$

**THERMAL RESISTANCE**

From junction to ambient	$R_{th\ j-a}$	=	500 K/W
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**CHARACTERISTICS**

$T_j = 25^\circ\text{C}$  unless otherwise specified

*Collector cut-off current*

$I_E = 0; -V_{CB} = 20 \text{ V}$	$-I_{CB0}$	<	100 nA
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$I_E = 0; -V_{CB} = 20 \text{ V}; T_j = 100^\circ\text{C}$	$-I_{CB0}$	<	10 $\mu\text{A}$
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*Base-emitter voltage*

$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$	$-V_{BE}$		600 to 750 mV
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*Saturation voltages*

$-I_C = 10 \text{ mA}; -I_B = 0,5 \text{ mA}$	$-V_{CEsat}$	typ.	80 mV
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< 300 mV

$-V_{BEsat}$	typ.	720 mV
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$-I_C = 50 \text{ mA}; -I_B = 2,5 \text{ mA}$	$-V_{CEsat}$	typ.	150 mV
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$-V_{BEsat}$	typ.	810 mV
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*D.C. current gain*

$-I_C = 10 \mu\text{A}; -V_{CE} = 5 \text{ V}$	$h_{FE}$	typ.	<b>BCW69</b> 90	<b>BCW70</b> 150
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$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$	$h_{FE}$	>	120	215
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*Collector capacitance at  $f = 1 \text{ MHz}$*

$I_E = I_e = 0; -V_{CB} = 10 \text{ V}$	$C_c$	typ.	4,5	pF
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*Transition frequency at  $f = 35 \text{ MHz}$*

$-I_C: 10 \text{ mA}; -V_{CE} = 5 \text{ V}$	$f_T$	typ.	150	MHz
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*Noise figure at  $R_S = 2 \text{ k}\Omega$*

$-I_C = 200 \mu\text{A}; -V_{CE} = 5 \text{ V}$	$F$	<	10	dB
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$f = 1 \text{ kHz}; B = 200 \text{ Hz}$



## Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
SOT-23 T&R	3K/reel	136 gm/3K pcs	3" x 7.5" x 7.5"	12.0K	17" x 15" x 13.5"	192.0K	12 kgs
			9" x 9" x 9"	51.0K	19" x 19" x 19"	408.0K	28 kgs
	10K/reel	415 gm/10K pcs	13" x 13" x 0.5"	10.0K	17" x 15" x 13.5"	300.0K	16 kgs

## Customer Notes

### Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

## Disclaimer

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